

Optical and Electrical Diagnostics of a High-Voltage Laser-Triggered Switch with Variable Impedance Load

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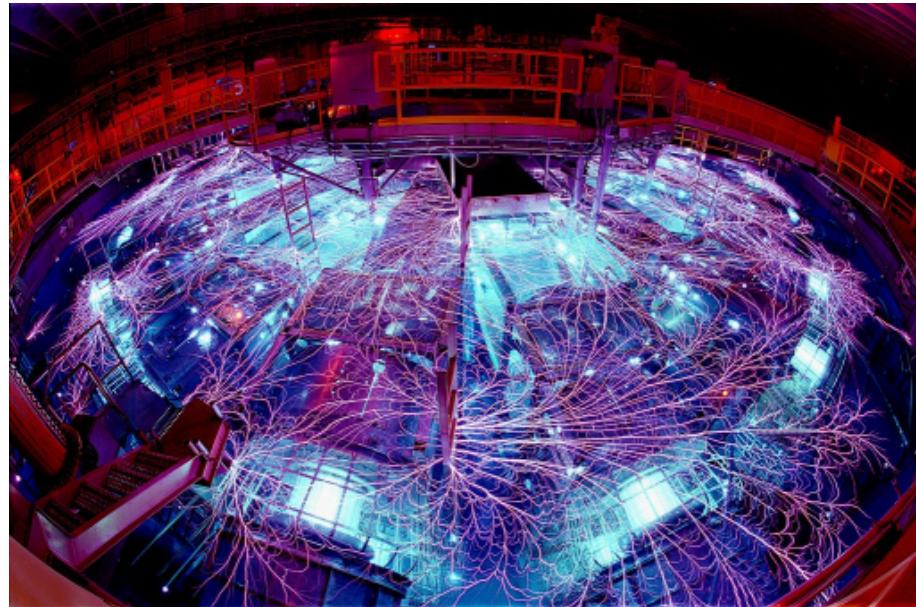
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Introduction to Pulsed Power

- kV to MV potentials kA to MA currents
- Hundred Nanosecond scale pulses
- High-Voltage Laser-Triggered Switch
 - Time Repeatability and Jitter ~ nanoseconds
 - Single Laser, Many Switches
- Used to produce extreme temperatures and pressures
 - High Energy Physics
 - Fusion



Sandia National Labs Z Machine
Credit: <https://www.sandia.gov/z-machine/>

Theory

Braginskii model power balance [1]:

$$\frac{I}{\sigma} = 2\pi^2 \rho_0 \xi (a \dot{a})^3$$

Martin Model [2]:

$$a^2 = \left(\frac{4}{\pi^2 \rho_0 \xi \sigma} \right)^{\frac{1}{3}} \int_0^t I^{2/3} dt \quad R_{Plasma} = \frac{L}{\sigma \pi a^2}$$

Spitzer Resistivity [3]:

$$\eta = \frac{1}{\sigma} = \frac{2\sqrt{2\pi}}{3} \frac{Ze^2 \sqrt{m_e} \ln \Lambda}{(4\pi\epsilon_0)^2 (k_B T_e)^{3/2}}$$

I – Current

σ – Plasma Conductivity

η – Plasma Resistivity

ρ_0 – Gas Density

ξ – Dimensionless Constant

a – Plasma Channel Radius

\dot{a} – Rate of Plasma Channel Radial Growth

L – Plasma Channel Length

e – Elemental Charge

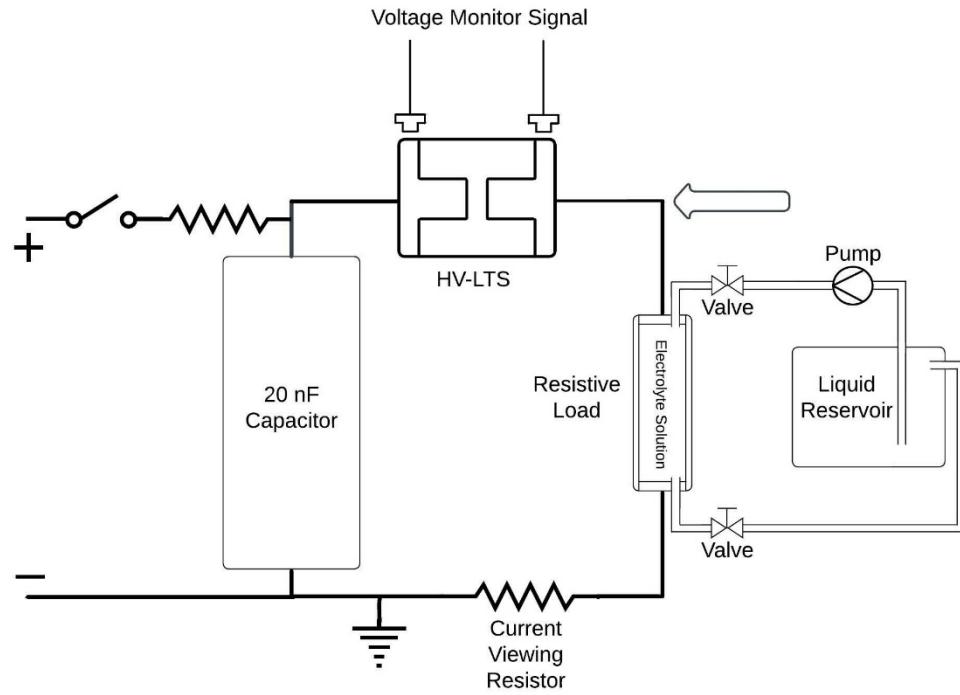
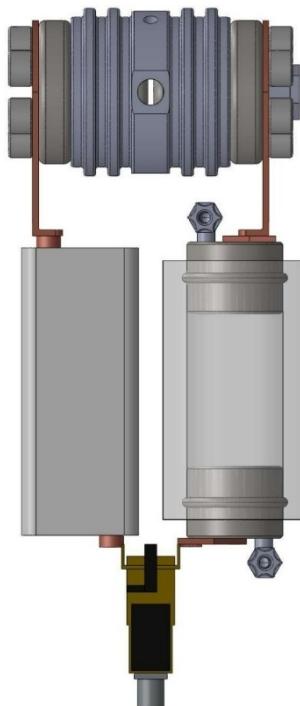
m_e – Electron Mass

$\ln \Lambda$ – Coulomb Logarithm

T_e – Electron Temperature

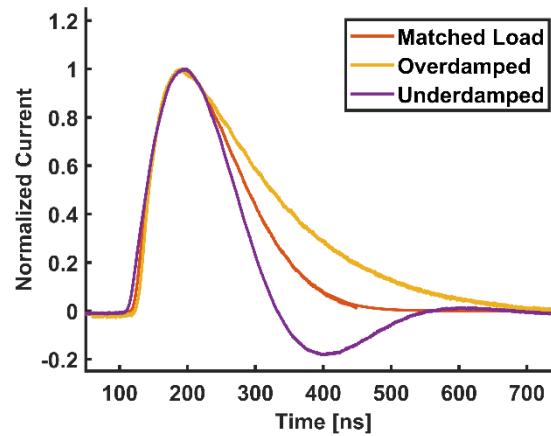
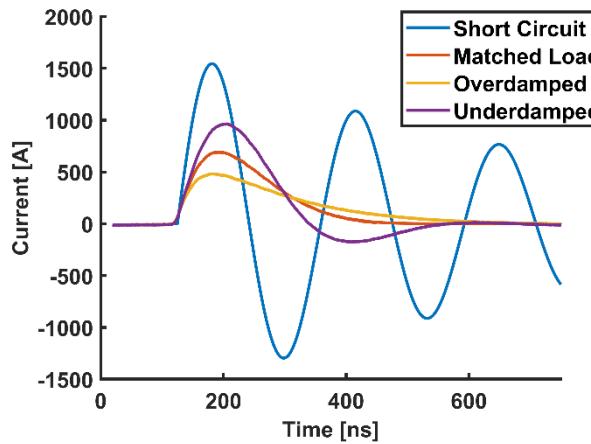
High-Voltage Switch Testbed with a Variable Impedance Load

- 3.5 mm Spark-Gap
- Ambient Pressure & Temperature
- 5 – 6 kV Operation
- Tunable Load 2 – 10 Ω



High-Voltage Switch Testbed with a Variable Impedance Load

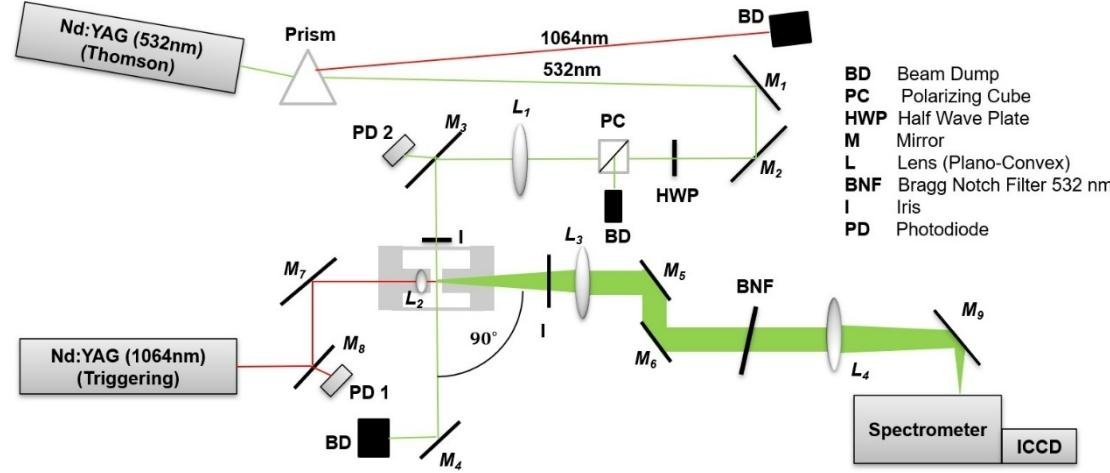
- Impedance is Tuned to Switch Conditions
- Rising-Edge Determined by Pulse Forming Network



Time Zero is defined by the time of the triggering laser pulse

Experimental Design – Laser Thomson Scattering

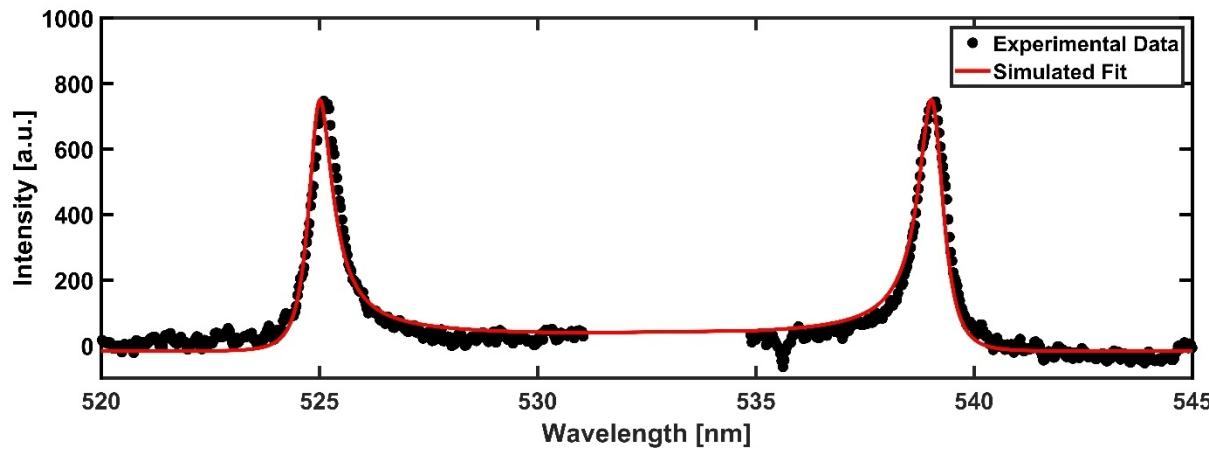
- Laser Thomson Scattering
 - Electron Temperature (Plasma Conductivity)
 - Electron Density
- No Assumptions Needed



Experimental Design – Laser Thomson Scattering

Salpeter Approximation Ignoring Ion Contribution

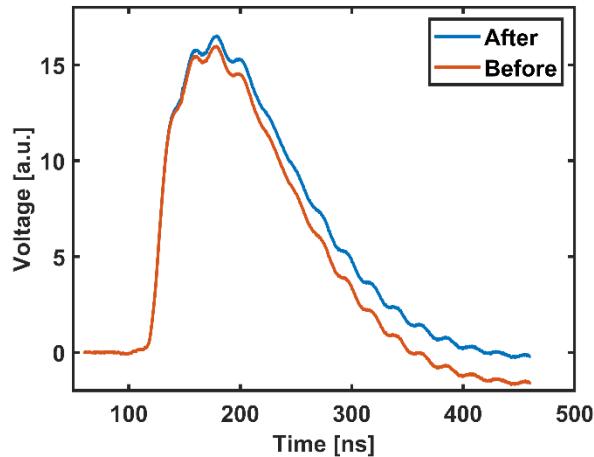
$$S(\mathbf{k}, \omega) \approx \frac{\sqrt{2\pi}}{\nu_{te}} \Gamma_\alpha(\xi_e)$$



Experimental Design – Electrical Diagnostics

- Non-contact Derivative Coupled Voltage Monitors (V-Dot Probes)
- No Affect on Switch Performance
 - No Path to Ground
- Require Integration
 - Numerical
 - Oscilloscope May Alias High Frequency Data
 - **Analog RC Circuit Integrator**
 - Requires Droop Correction

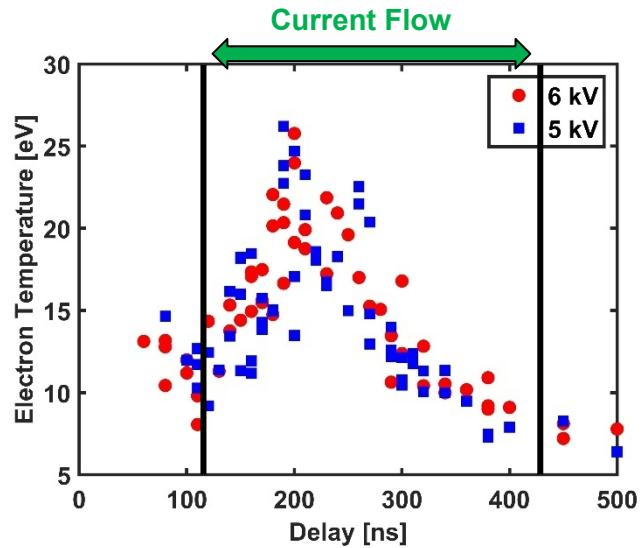
$$S(t)_{corrected} = S(t) + \frac{3}{2\tau} \int_{t_{start}}^t S(t') dt'$$



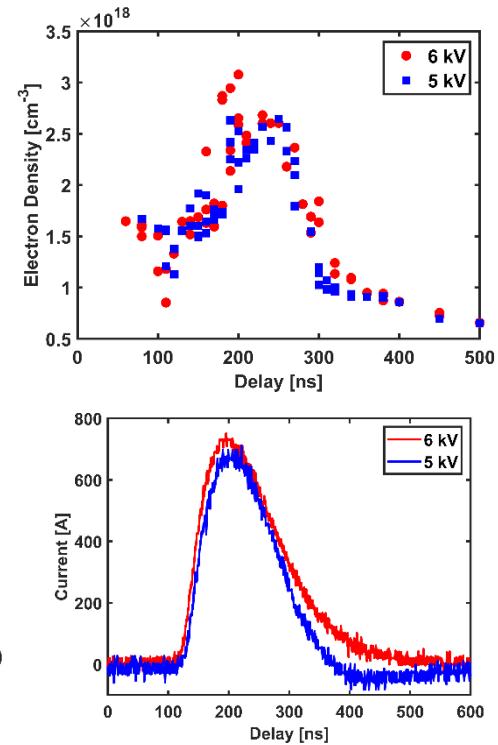
Results – Optical Diagnostics

Laser Thomson Scattering

- Electron Temperature Does Not Stabilize
- Changing Plasma Conductivity

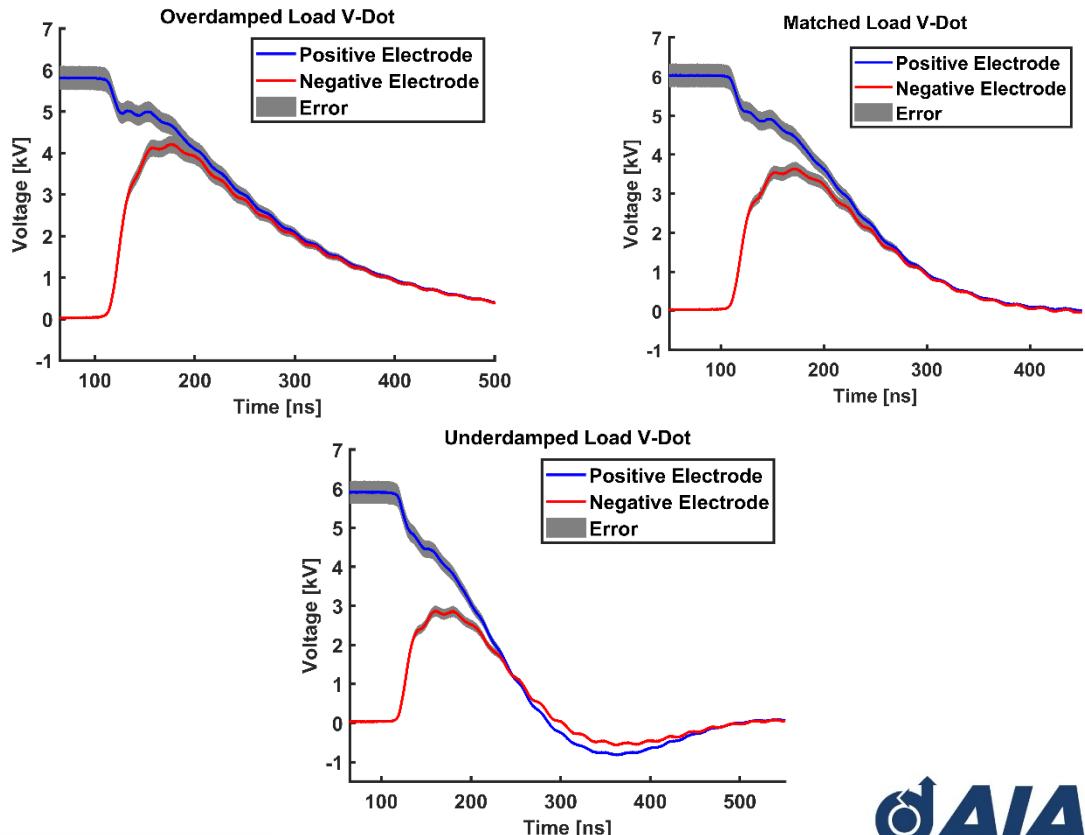


± 20% Error



Results – Electrical Diagnostics

- Capacitor Charged to 6 kV
- Load Impedance Changed

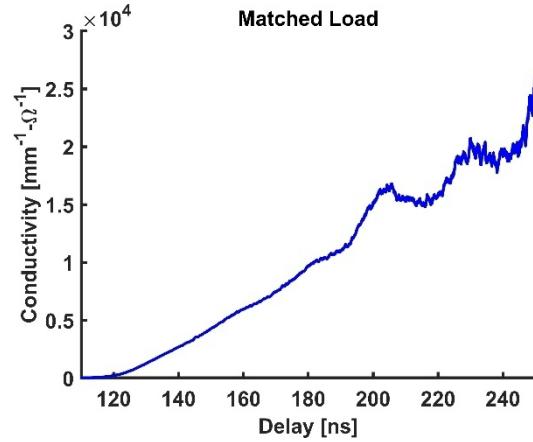
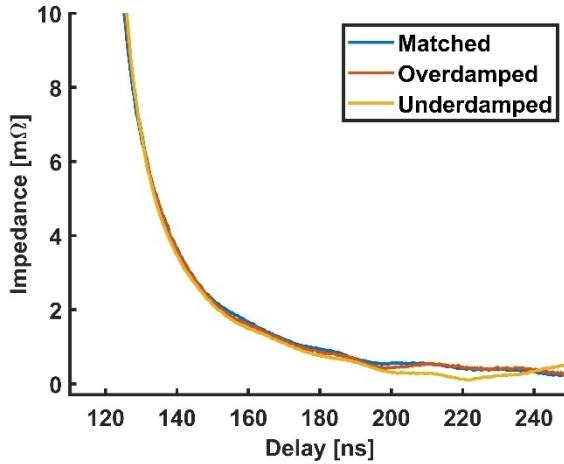


Results – Electrical Diagnostics

- Plasma Channel Impedance Collapse Determined by Pulse Forming Network (Not Load)
- The Plasma Channel Conductivity is Not Constant

$$R_{Plasma} = \frac{V_{drop}}{I}$$

$$R_{Plasma} = \frac{L}{\sigma \pi r^2}$$

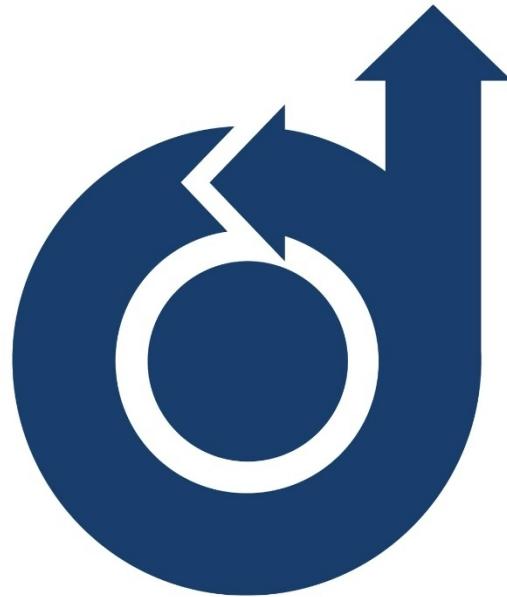


Conclusion

- Optical Measurements Show a Changing Electron Temperature and In Turn The Calculated Plasma Conductivity
- Electrical Measurements Show an Increasing Plasma Conductivity During Rising Edge of Current Pulse
- Assumption of a Temporally Constant Plasma Conductivity in the Martin/Braginskii Model is not accurate for this operating regime

Acknowledgements

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Additional Slides

➤ Thomson Scattering Simulation

the scattering form factor, $S(\mathbf{k}, \omega)$, is used^{37,40}:

$$S(\mathbf{k}, \omega) \approx \frac{\sqrt{2\pi}}{v_{te}} \Gamma_\alpha(\xi_e) \quad (2)$$

where the line shape function, Γ_α , is:

$$\Gamma_\alpha(\xi_e) = \frac{\exp(-\xi_e^2)}{|1 + \alpha^2 w(\xi_e)|^2} \quad (3)$$

where the plasma dispersion function, $w(\xi)$, is⁴¹:

$$w(\xi) = 1 - 2\xi_e e^{-\xi_e^2} \int_0^{\xi_e} e^{-\zeta^2} d\zeta + i\pi^{\frac{1}{2}} \xi_e e^{-\xi_e^2} \quad (4)$$

where the ratio, ξ_e , of wave phase velocity to the electron thermal velocity is⁴¹:

$$\xi_e = \frac{\omega_{pl}}{k v_{te} \sqrt{2}} \quad (5)$$

and the electron thermal velocity, v_{te} , is:

$$v_{te} = \sqrt{\frac{8k_B T_e}{\pi m_e}} \quad (6)$$